

2SK3140

Silicon N Channel MOS FET
High Speed Power Switching

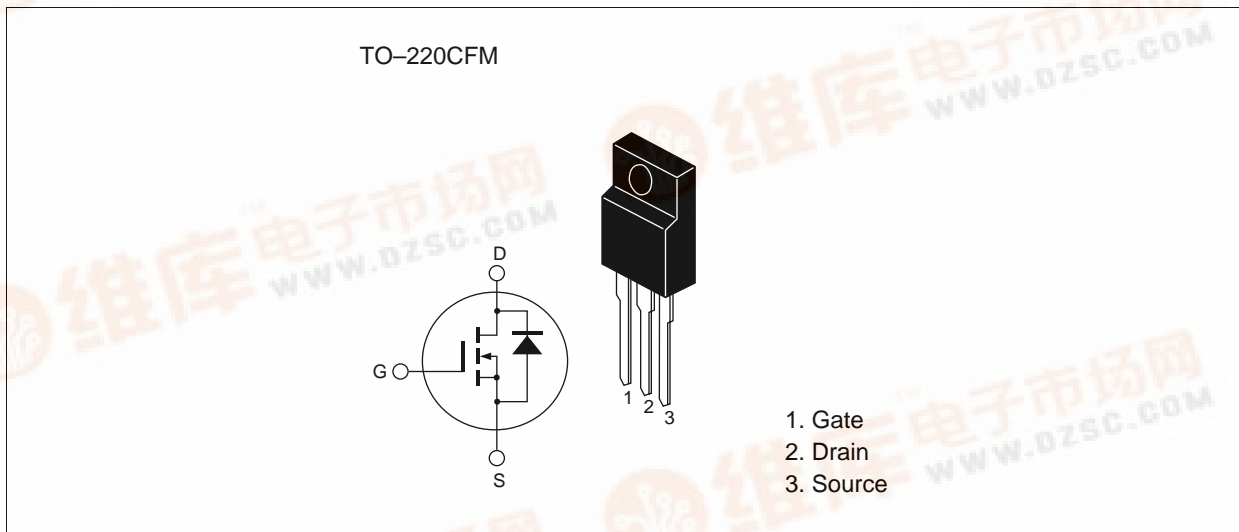
HITACHI

ADE-208-767C (Z)
4th. Edition
February 1999

Features

- Low on-resistance
 $R_{DS(on)} = 6 \text{ m}\Omega$ typ.
- Low drive current
- 4 V gate drive device can be driven from 5 V source

Outline



2SK3140

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	60	A
Drain peak current	I _{D(pulse)} ^{Note 1}	240	A
Body-drain diode reverse drain current	I _{DR}	60	A
Avalanche current	I _{AP} ^{Note 3}	50	A
Avalanche energy	E _{AR} ^{Note 3}	214	mJ
Channel dissipation	Pch ^{Note 2}	35	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

- Note: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg $\geq 50 \Omega$

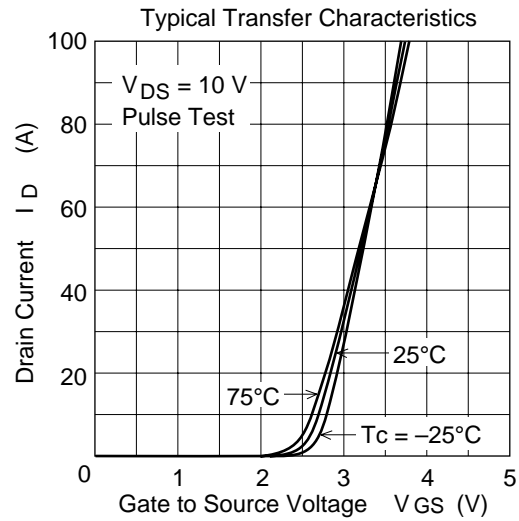
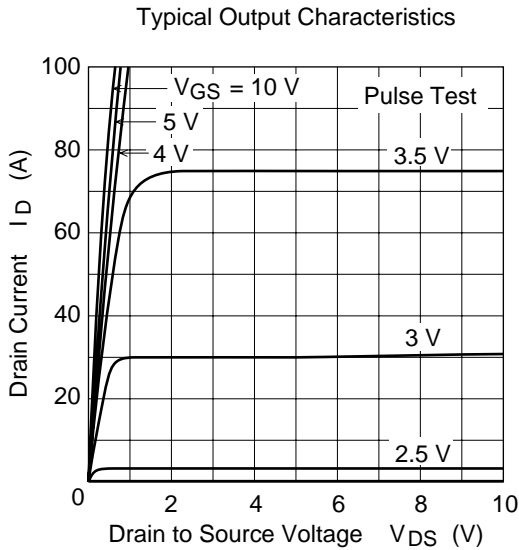
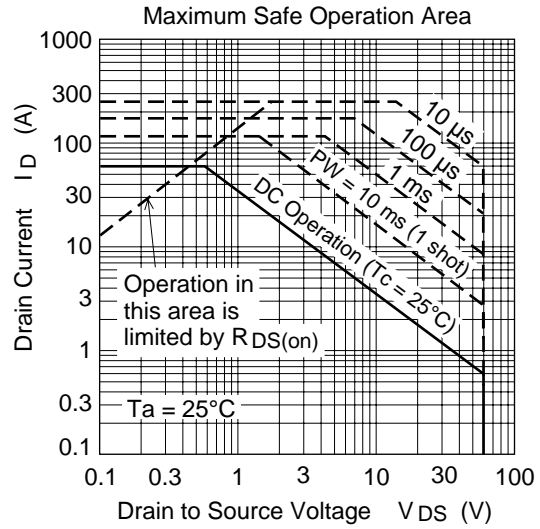
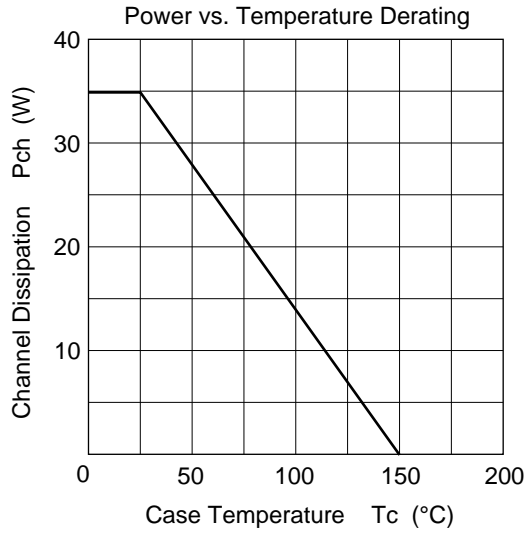
Electrical Characteristics (Ta = 25°C)

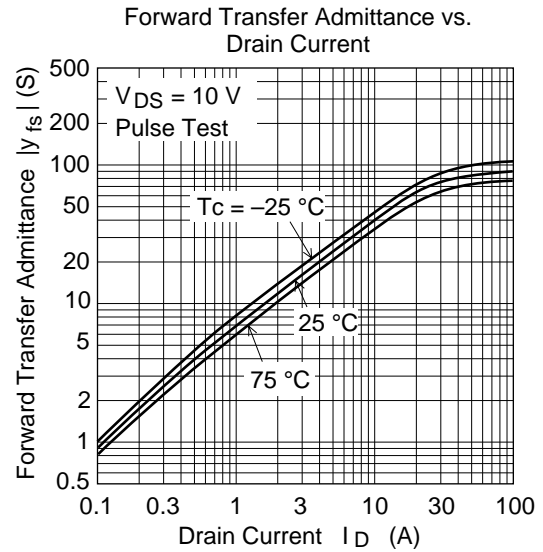
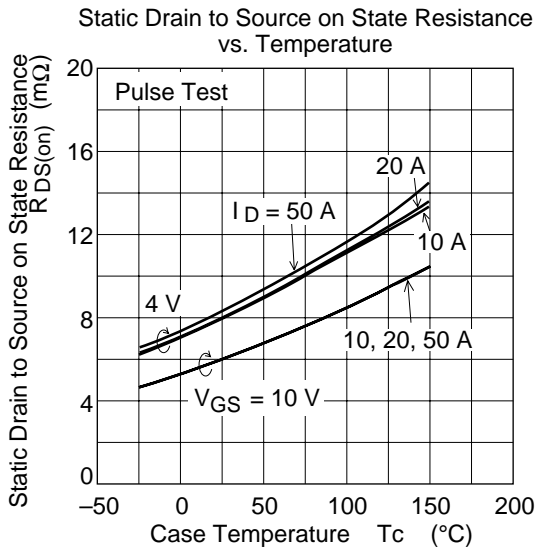
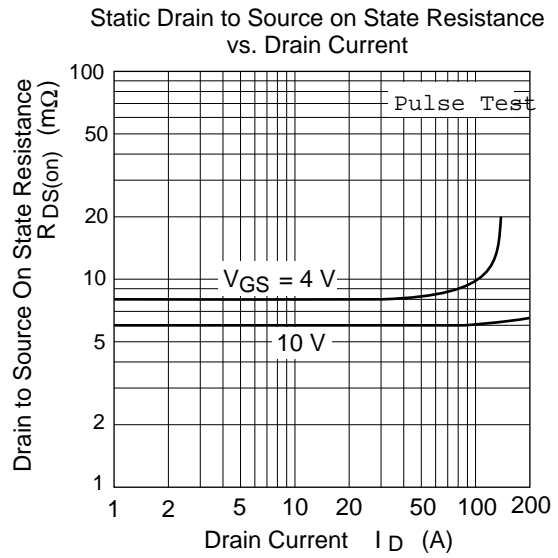
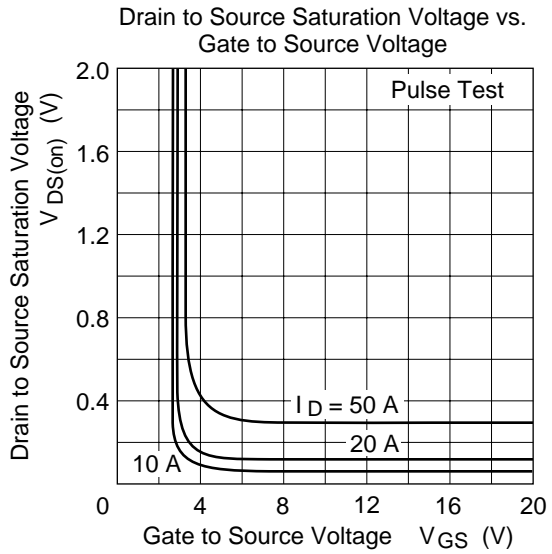
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$ <small>Note 1</small>
Static drain to source on state resistance	$R_{DS(on)}$	—	6.0	7.5	$\text{m}\Omega$	$I_D = 30 \text{ A}$, $V_{GS} = 10 \text{ V}$ <small>Note 1</small>
		—	8.0	12	$\text{m}\Omega$	$I_D = 30 \text{ A}$, $V_{GS} = 4 \text{ V}$ <small>Note 1</small>
Forward transfer admittance	$ y_{fs} $	45	75	—	S	$I_D = 30 \text{ A}$, $V_{DS} = 10 \text{ V}$ <small>Note 1</small>
Input capacitance	C_{iss}	—	7100	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	1000	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	280	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	125	—	nc	$V_{DD} = 25 \text{ V}$
Gate to source charge	Q_{gs}	—	25	—	nc	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	25	—	nc	$I_D = 60 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	60	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 30 \text{ A}$
Rise time	t_r	—	250	—	ns	$R_L = 1 \Omega$
Turn-off delay time	$t_{d(off)}$	—	540	—	ns	
Fall time	t_f	—	320	—	ns	
Body-drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 60 \text{ A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	80	—	ns	$I_F = 60 \text{ A}$, $V_{GS} = 0$ $diF/dt = 50 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

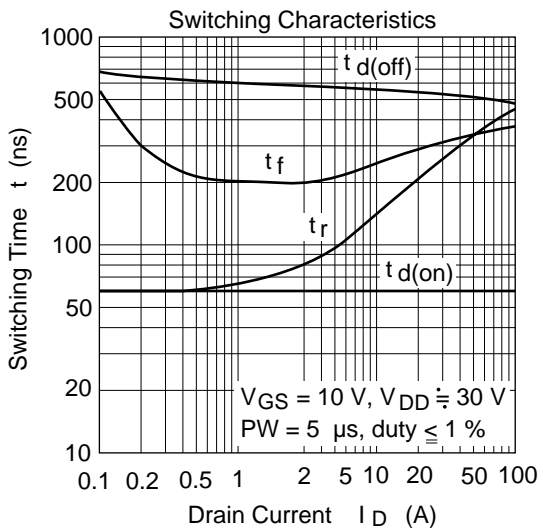
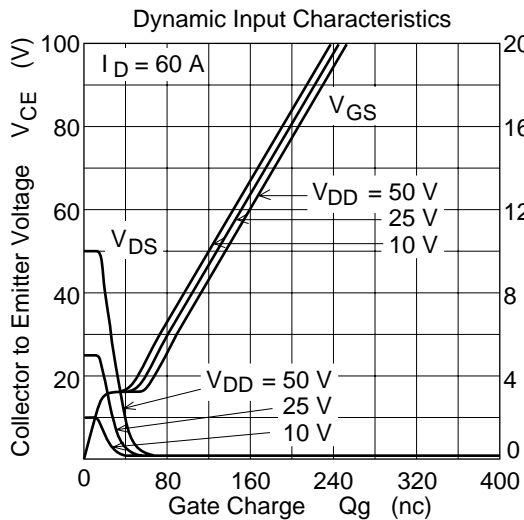
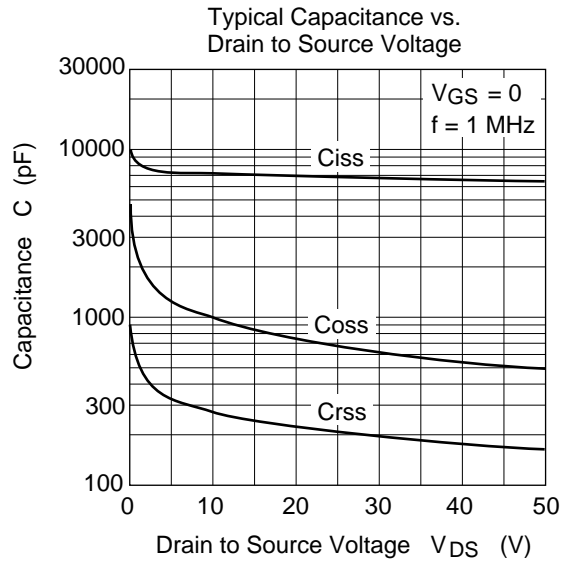
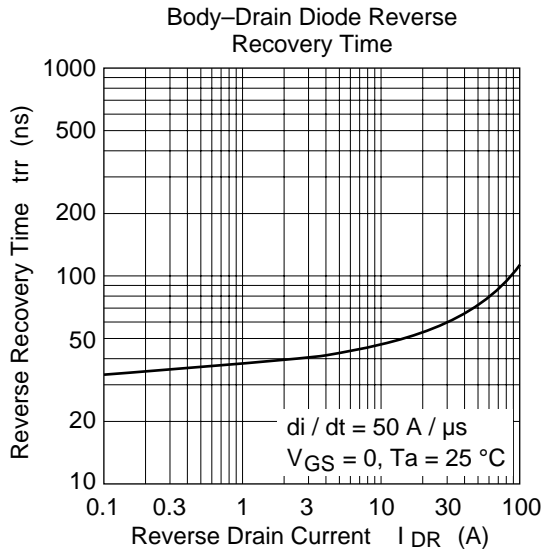
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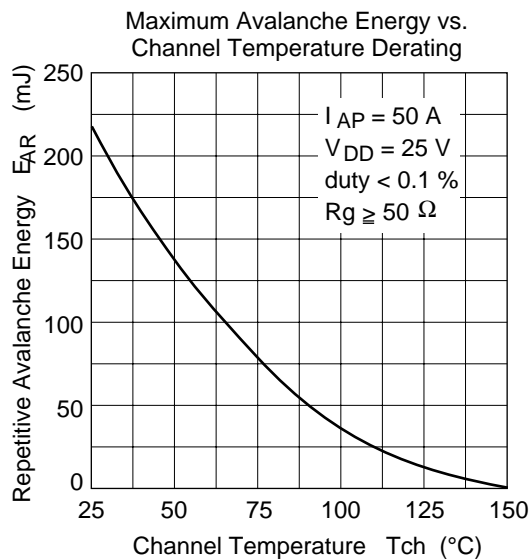
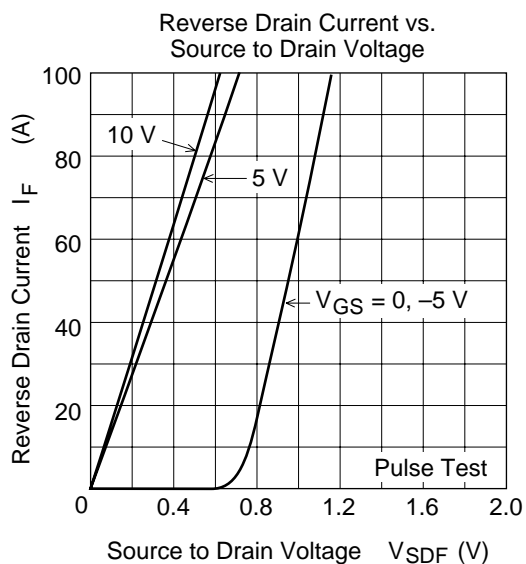
Main Characteristics



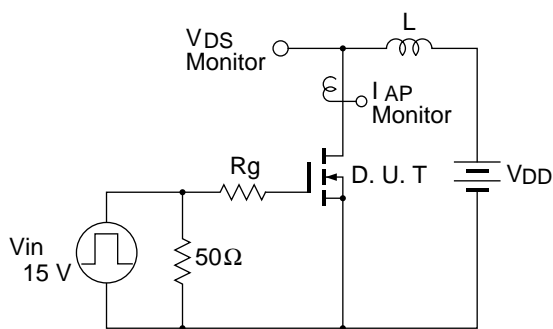


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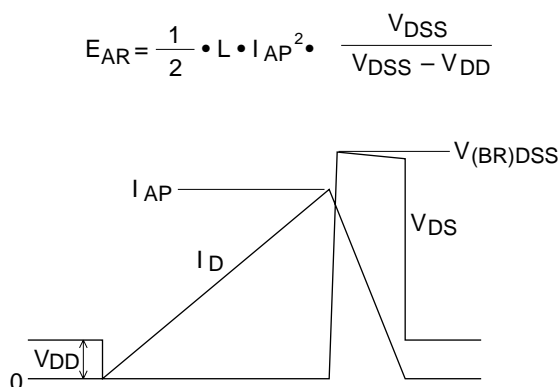




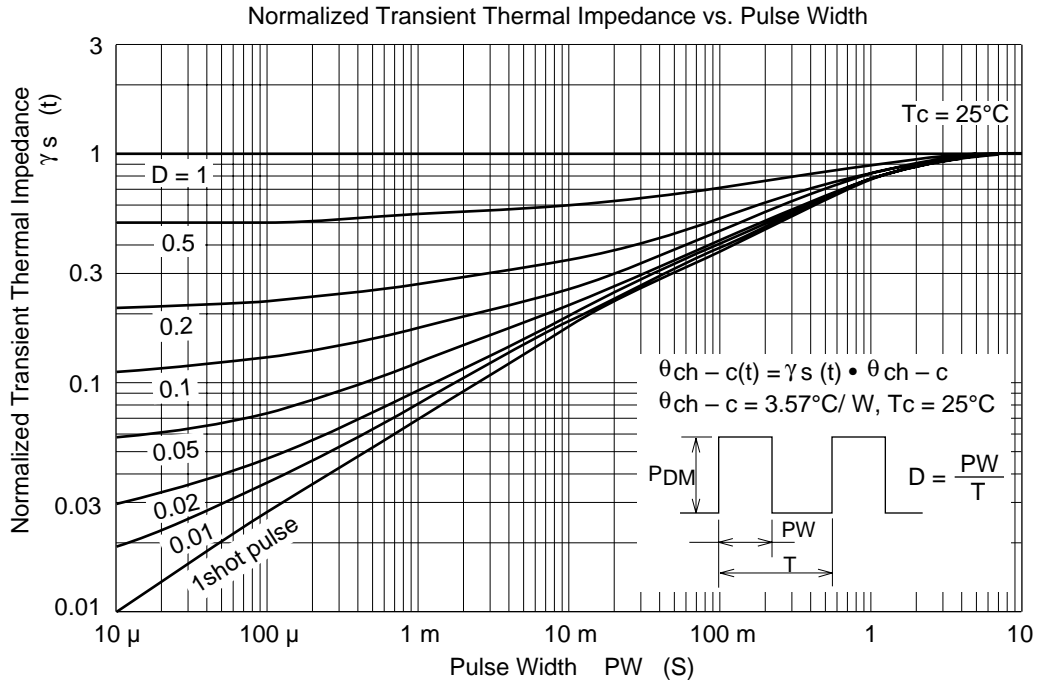
Avalanche Test Circuit



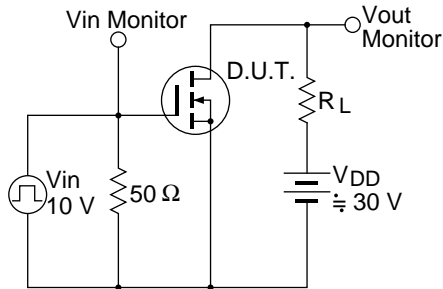
Avalanche Waveform



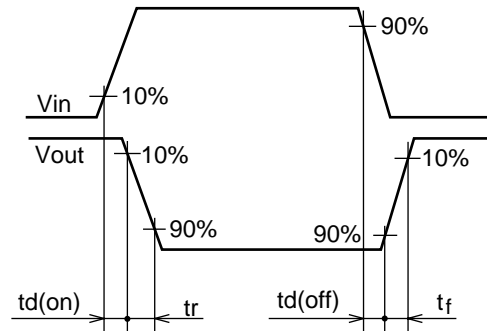
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Switching Time Test Circuit

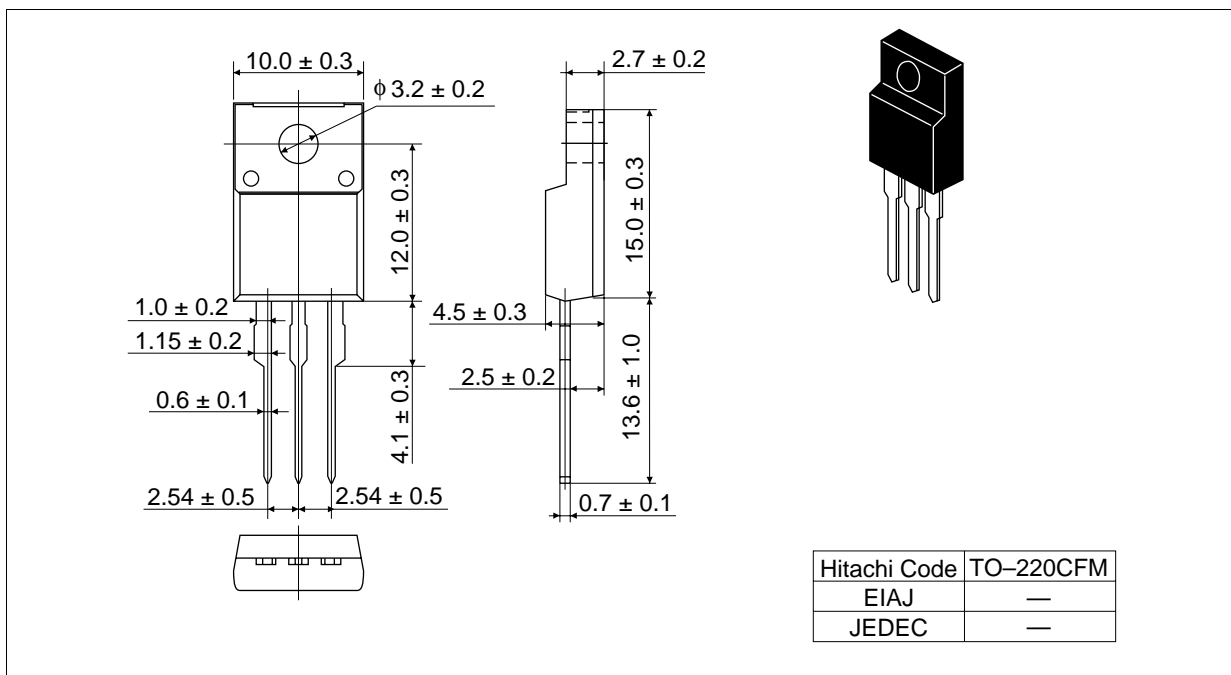


Waveform



Package Dimensions

Unit: mm



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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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